

TRISIL™ FOR TELECOM EQUIPMENT PROTECTION

FEATURES

- Bidirectional crowbar protection
- Voltage range from 62V to 270V
- Low capacitance from 10pF to 20pF typ. @ 50V
- Low leakage current: $I_R = 2\mu\text{A}$ max.
- Holding current: $I_H = 150$ mA min.
- Repetitive peak pulse current:
 $I_{PP} = 30$ A (10/1000 μs)

MAIN APPLICATIONS

Telecommunication equipment such as:

- Analog and digital line cards (xDSL, T1/E1, ISDN...).
- Terminals (phone, fax, modem...) and central office equipment.

DESCRIPTION

The SMP30-xxx series has been designed to protect telecommunication equipment against lightning and transient induced by AC power lines. The package / die size ratio has been optimized by using the SMA package.

BENEFITS

Trisils are not subject to ageing and provide a fail safe mode in short circuit for a better protection. They are used to help equipment to meet various standards such as UL1950, IEC950 / CSA C22.2, UL1459 and FCC part 68.

Trisils have UL94 V0 approved resin.

SMA package is JEDEC registered (DO-214AC).

Trisils are UL497B approved (file: E136224).

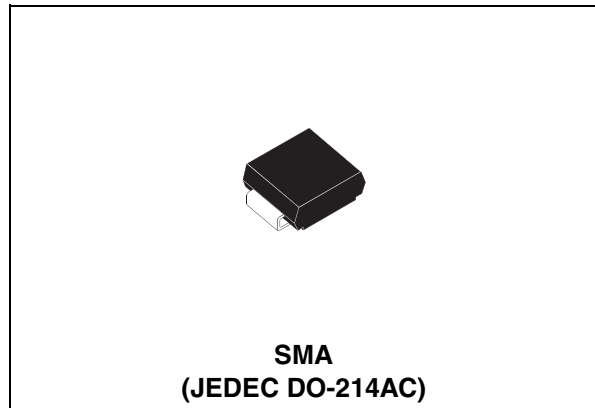


Table 1: Order Codes

Part Number	Marking
SMP30-62	QAA
SMP30-68	QAB
SMP30-100	QAC
SMP30-120	QAD
SMP30-130	QAE
SMP30-180	QAF
SMP30-200	QAG
SMP30-220	QAH
SMP30-240	QAI
SMP30-270	QAJ

Figure 1: Schematic Diagram

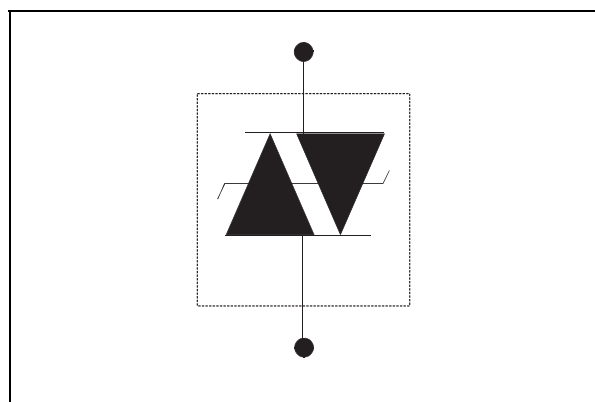


Table 2: In compliance with the following standards

STANDARD	Peak Surge Voltage (V)	Waveform Voltage	Required peak current (A)	Current waveform	Minimum serial resistor to meet standard (Ω)
GR-1089 Core First level	2500	2/10 μ s	500	2/10 μ s	20
	1000	10/1000 μ s	100	10/1000 μ s	24
GR-1089 Core Second level	5000	2/10 μ s	500	2/10 μ s	40
GR-1089 Core Intra-building	1500	2/10 μ s	100	2/10 μ s	0
ITU-T-K20/K21	6000 1500	10/700 μ s	150 37.5	5/310 μ s	110 0
ITU-T-K20 (IEC61000-4-2)	8000 15000	1/60 ns	ESD contact discharge ESD air discharge		0 0
VDE0433	4000	10/700 μ s	100	5/310 μ s	60
	2000		50		10
VDE0878	4000	1.2/50 μ s	100	1/20 μ s	18
	2000		50		0
IEC61000-4-5	4000	10/700 μ s	100	5/310 μ s	60
	4000	1.2/50 μ s	100	8/20 μ s	18
FCC Part 68, lightning surge type A	1500	10/160 μ s	200	10/160 μ s	26
	800	10/560 μ s	100	10/560 μ s	15
FCC Part 68, lightning surge type B	1000	9/720 μ s	25	5/320 μ s	0

Table 3: Absolute Ratings ($T_{amb} = 25^{\circ}\text{C}$)

Symbol	Parameter		Value	Unit
I_{PP}	Repetitive peak pulse current (see figure 2)	10/1000 μ s	30	A
		8/20 μ s	70	
		10/560 μ s	35	
		5/310 μ s	40	
		10/160 μ s	45	
		1/20 μ s	70	
		2/10 μ s	100	
I_{FS}	Fail-safe mode : maximum current (note 1)	8/20 μ s	2.5	kA
I_{TSM}	Non repetitive surge peak on-state current (sinusoidal)	t = 0.2 s	14	A
		t = 1 s	10.5	
		t = 2 s	9	
		t = 15 mn	3	
I^2t	I^2t value for fusing	t = 16.6 ms	5.7	A^2s
		t = 20 ms	4.9	
T_{stg}	Storage temperature range		-55 to 150	$^{\circ}\text{C}$
T_j	Maximum junction temperature		150	
T_L	Maximum lead temperature for soldering during 10 s.		260	$^{\circ}\text{C}$

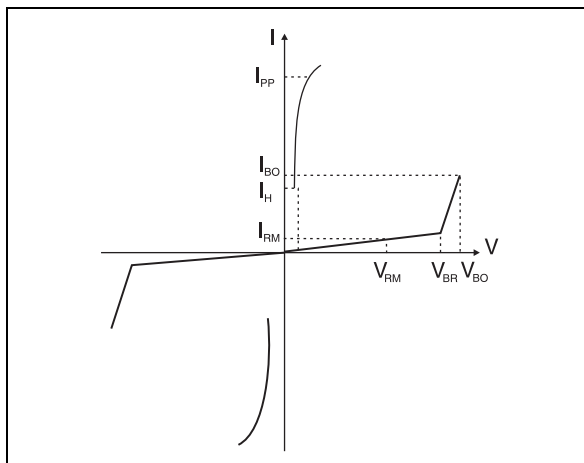
Note 1: in fail safe mode, the device acts as a short circuit.

Table 4: Thermal Resistances

Symbol	Parameter	Value	Unit
$R_{th(j-a)}$	Junction to ambient (with recommended footprint)	120	°C/W
$R_{th(j-l)}$	Junction to leads	30	°C/W

Table 5: Electrical Characteristics ($T_{amb} = 25^{\circ}\text{C}$)

Symbol	Parameter
V_{RM}	Stand-off voltage
V_{BR}	Breakdown voltage
V_{BO}	Breakover voltage
I_{RM}	Leakage current
I_{PP}	Peak pulse current
I_{BO}	Breakover current
I_H	Holding current
V_R	Continuous reverse voltage
I_R	Leakage current at V_R
C	Capacitance



Types	$I_{RM} @ V_{RM}$		$I_R @ V_R$		Dynamic	Static		I_H	C	C
	max.		max.		max.	max.	max.	min.	typ.	typ.
	μA	V	μA	V	V	V	mA	mA	pF	pF
SMP30-62	2	56	5	62	85	82	800	150	20	40
SMP30-68		61		68	93	90			20	40
SMP30-100		90		100	135	133			16	35
SMP30-120		108		120	160	160			16	30
SMP30-130		117		130	173	173			14	30
SMP30-180		162		180	235	240			12	25
SMP30-200		180		200	262	267			12	25
SMP30-220		198		220	285	293			10	20
SMP30-240		216		240	300	320			10	20
SMP30-270		243		270	350	360			10	20

Note 1: I_R measured at V_R guarantee $V_{BR} \min \geq V_R$

Note 2: see functional test circuit 1

Note 3: see test circuit 2

Note 4: see functional holding current test circuit 3

Note 5: $V_R = 50\text{V}$ bias, $V_{RMS}=1\text{V}$, $F=1\text{MHz}$

Note 6: $V_R = 2\text{V}$ bias, $V_{RMS}=1\text{V}$, $F=1\text{MHz}$

Figure 2: Pulse waveform

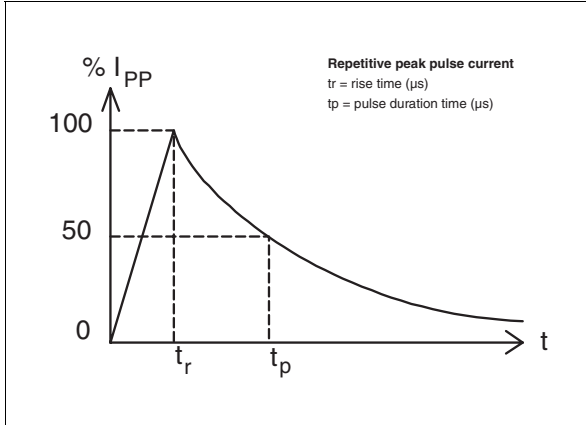


Figure 4: On-state voltage versus on-state current (typical values)

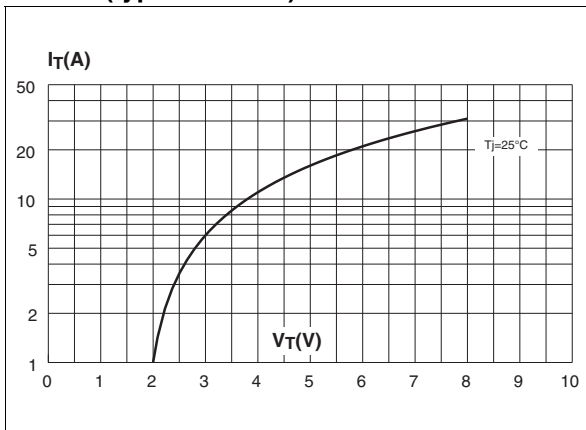


Figure 6: Relative variation of breakover voltage versus junction temperature

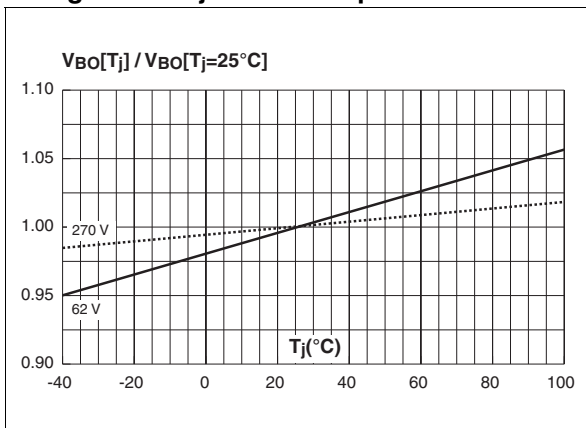


Figure 3: Non repetitive surge peak on-state current versus overload duration

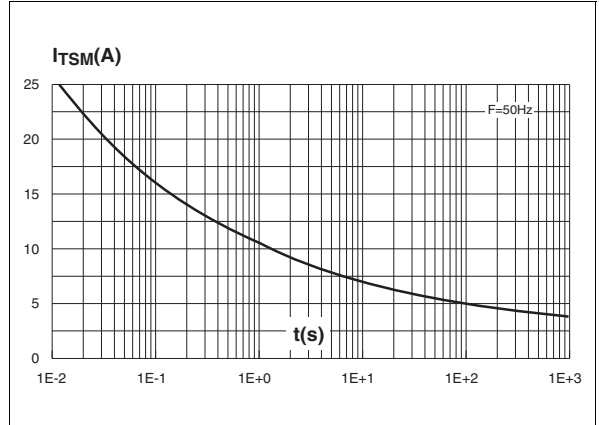


Figure 5: Relative variation of holding current versus junction temperature

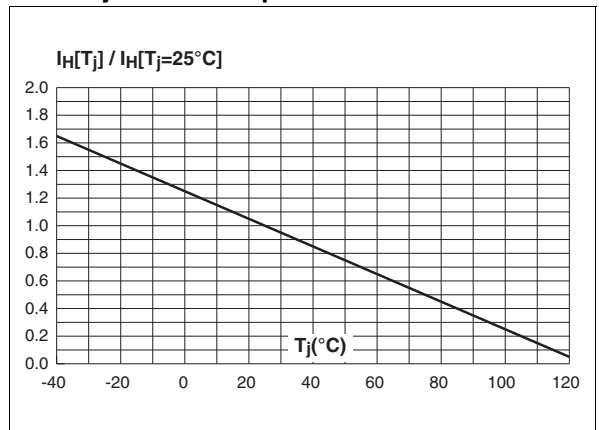


Figure 7: Relative variation of leakage current versus junction temperature (typical values)

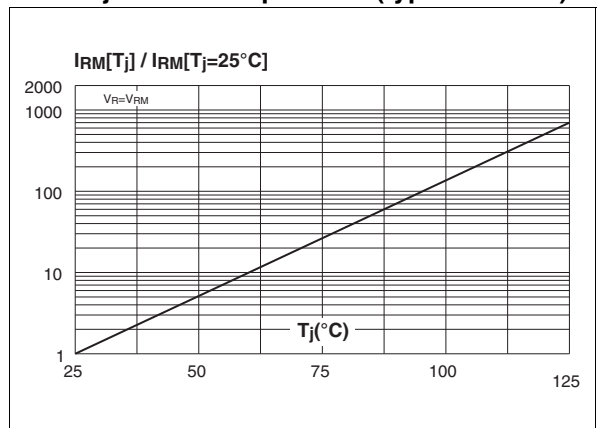


Figure 8: Variation of thermal impedance junction to ambient versus pulse duration (Printed circuit board FR4, SCu=35µm, recommended pad layout)

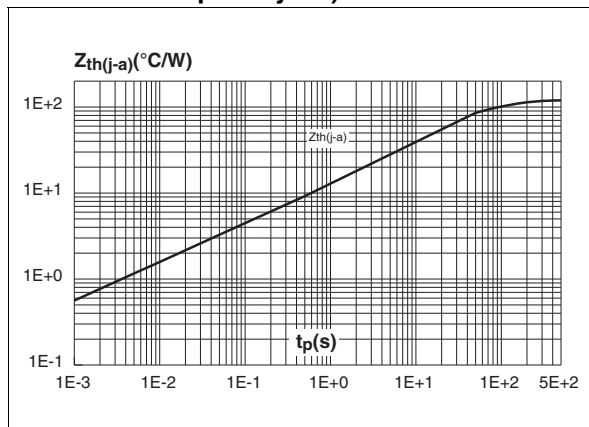


Figure 9: Relative variation of junction capacitance versus reverse voltage applied (typical values)

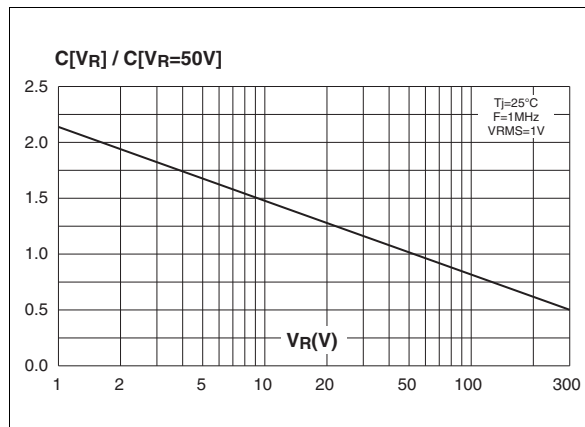


Figure 10: Test circuit 1 for dynamic I_{BO} and V_{BO} parameters

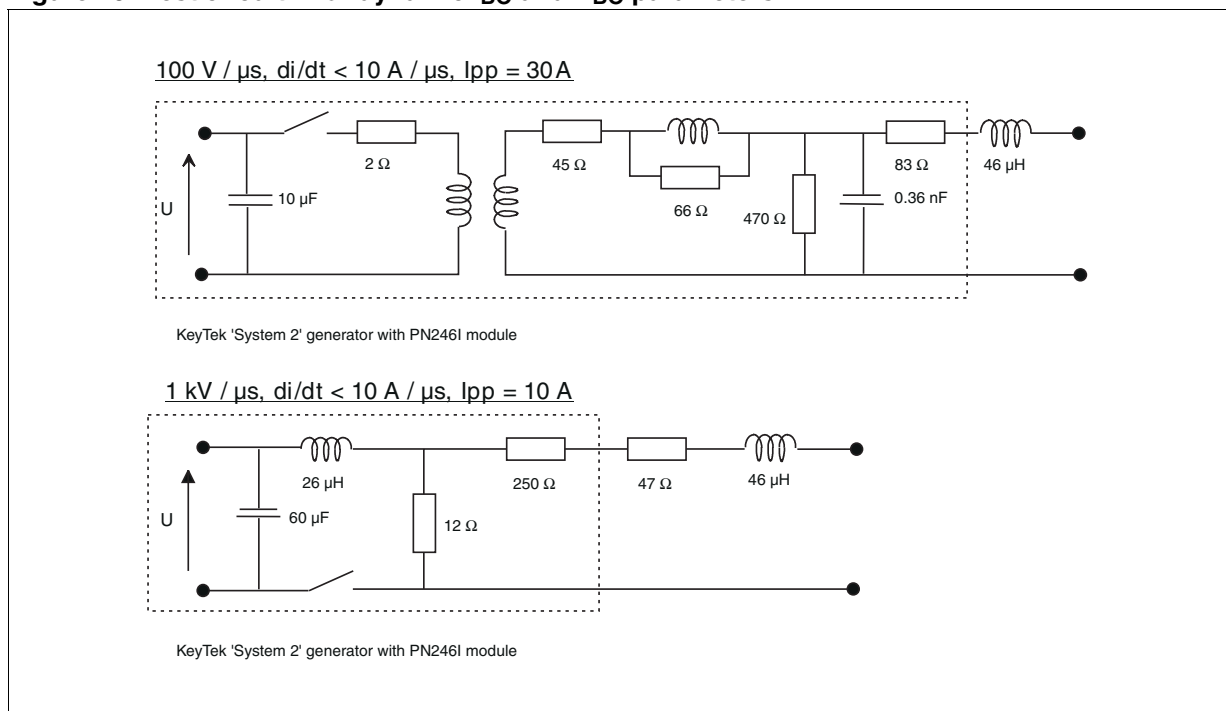


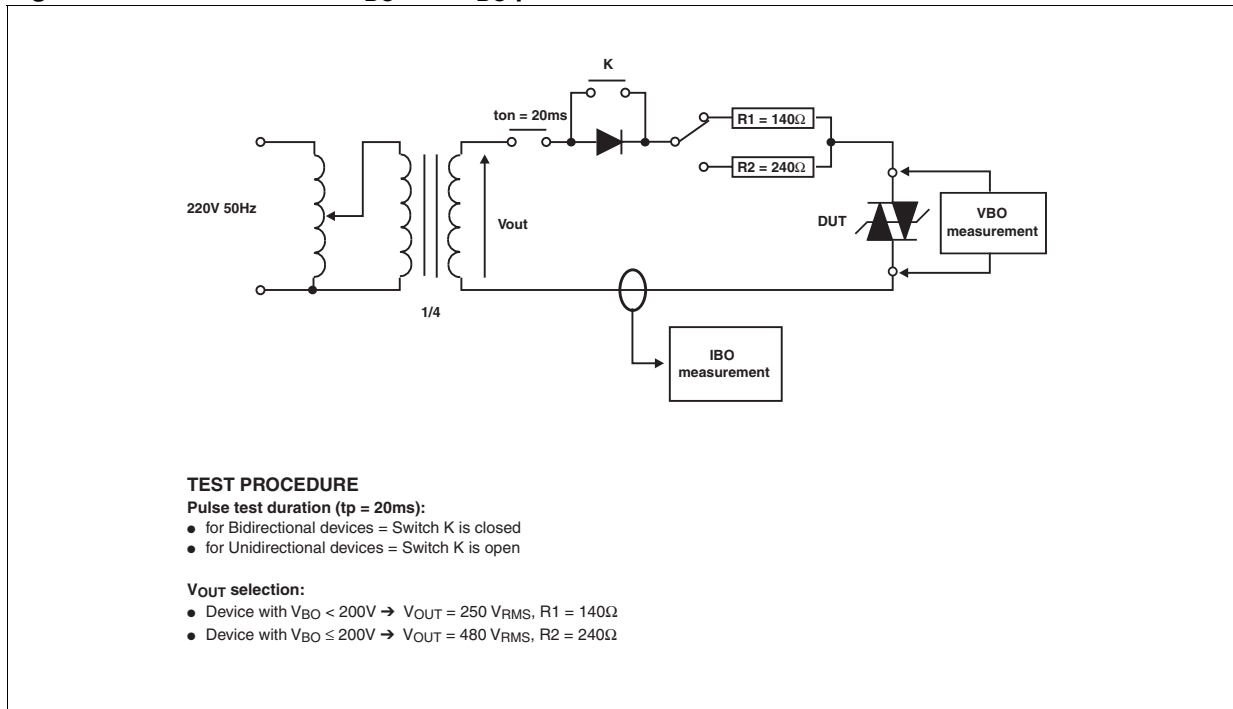
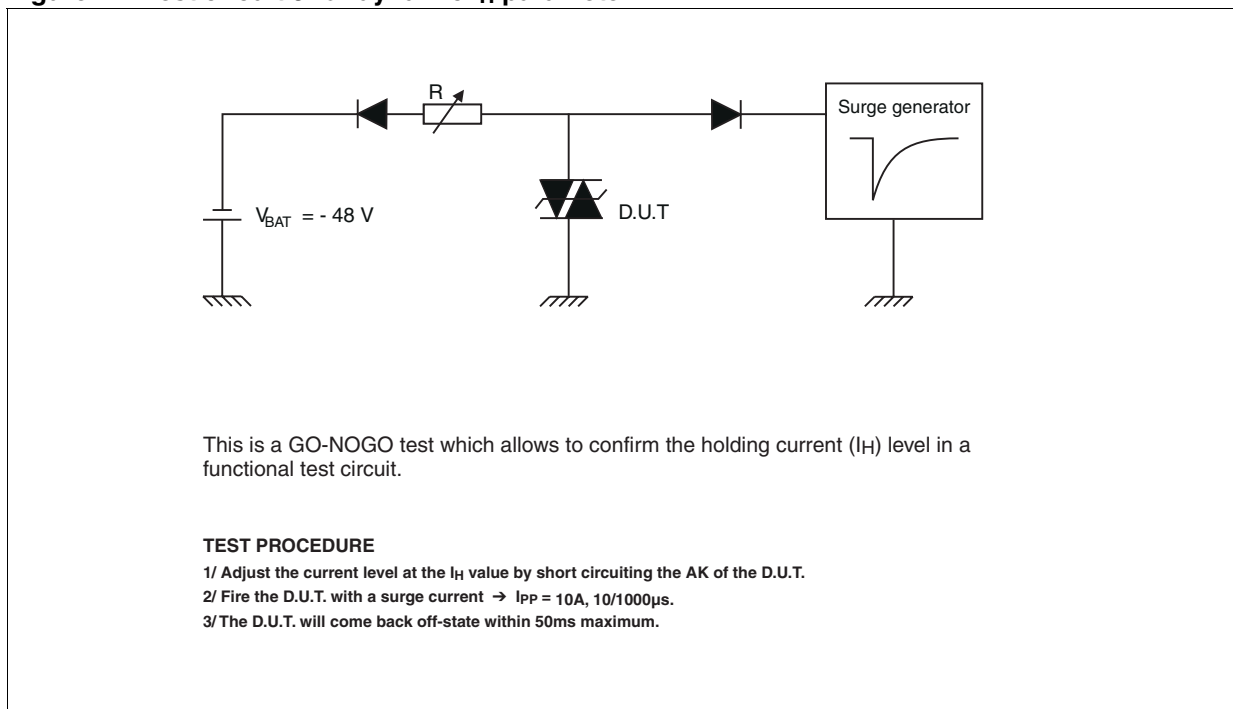
Figure 11: Test circuit 2 for I_{BO} and V_{BO} parametersFigure 12: Test circuit 3 for dynamic I_H parameter

Figure 13: Ordering Information Scheme

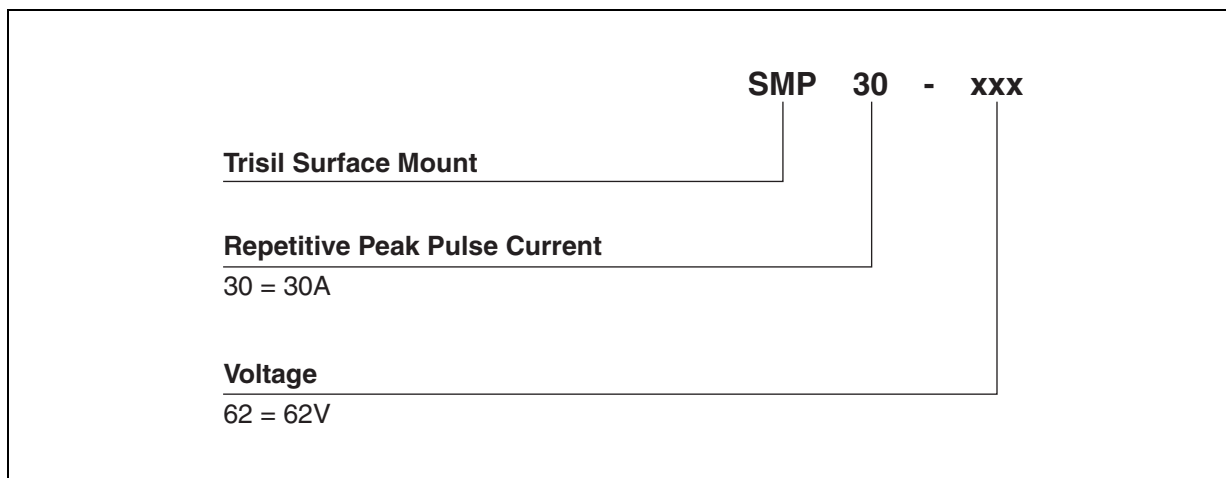


Figure 14: SMA Package Mechanical data

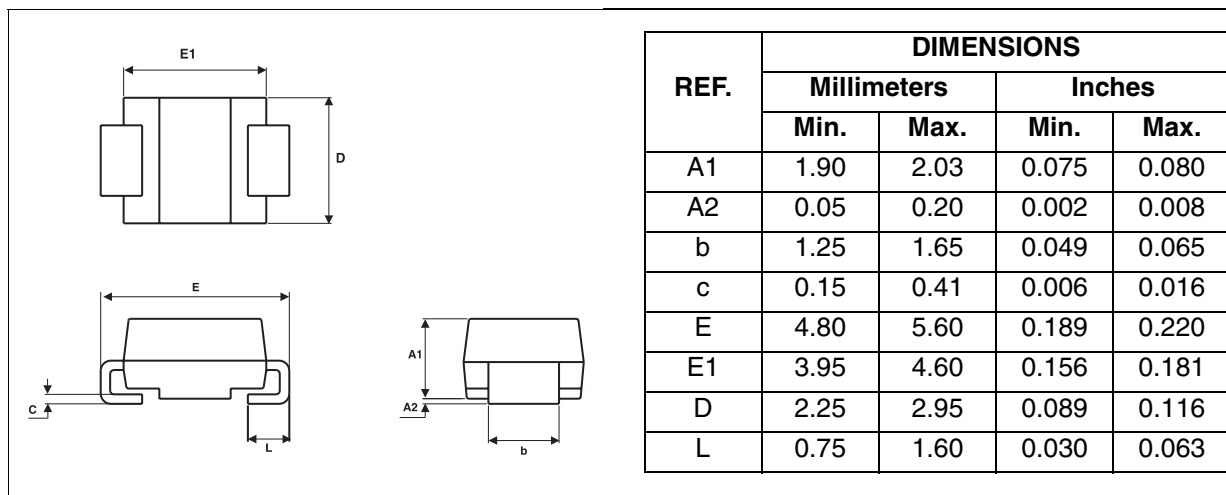
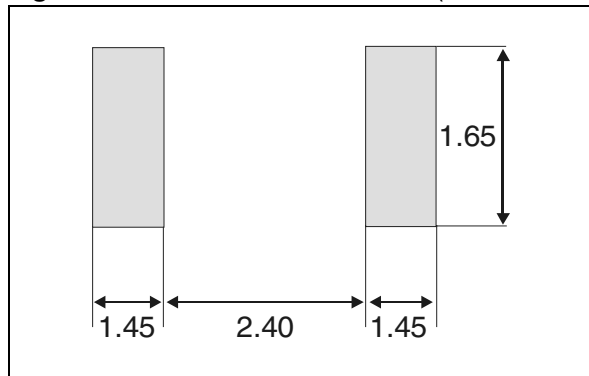


Figure 15: Foot Print Dimensions (in millimeters)



SMP30

Table 6: Ordering Information

Part Number	Marking	Package	Weight	Base qty	Delivery mode
SMP30-62	QAA	SMA	0.06 g	5000	Tape & reel
SMP30-68	QAB				
SMP30-100	QAC				
SMP30-120	QAD				
SMP30-130	QAE				
SMP30-180	QAF				
SMP30-200	QAG				
SMP30-220	QAH				
SMP30-240	QAI				
SMP30-270	QAJ				

Table 7: Revision History

Date	Revision	Description of Changes
November-2002	4B	Last update.
10-Nov-2004	5	SMA package dimensions update. Reference A1 max. changed from 2.70mm (0.106 inc.) to 2.03mm (0.080 inc.).
13-Dec-2004	6	Figure 7 text legend corrected from "... reverse voltage applied" to "... junction capacitance".

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